

Thermally Excited Ferromagnetic Resonance (TE-FMR) in Magnetic Tunnel Junctions (MTJs)

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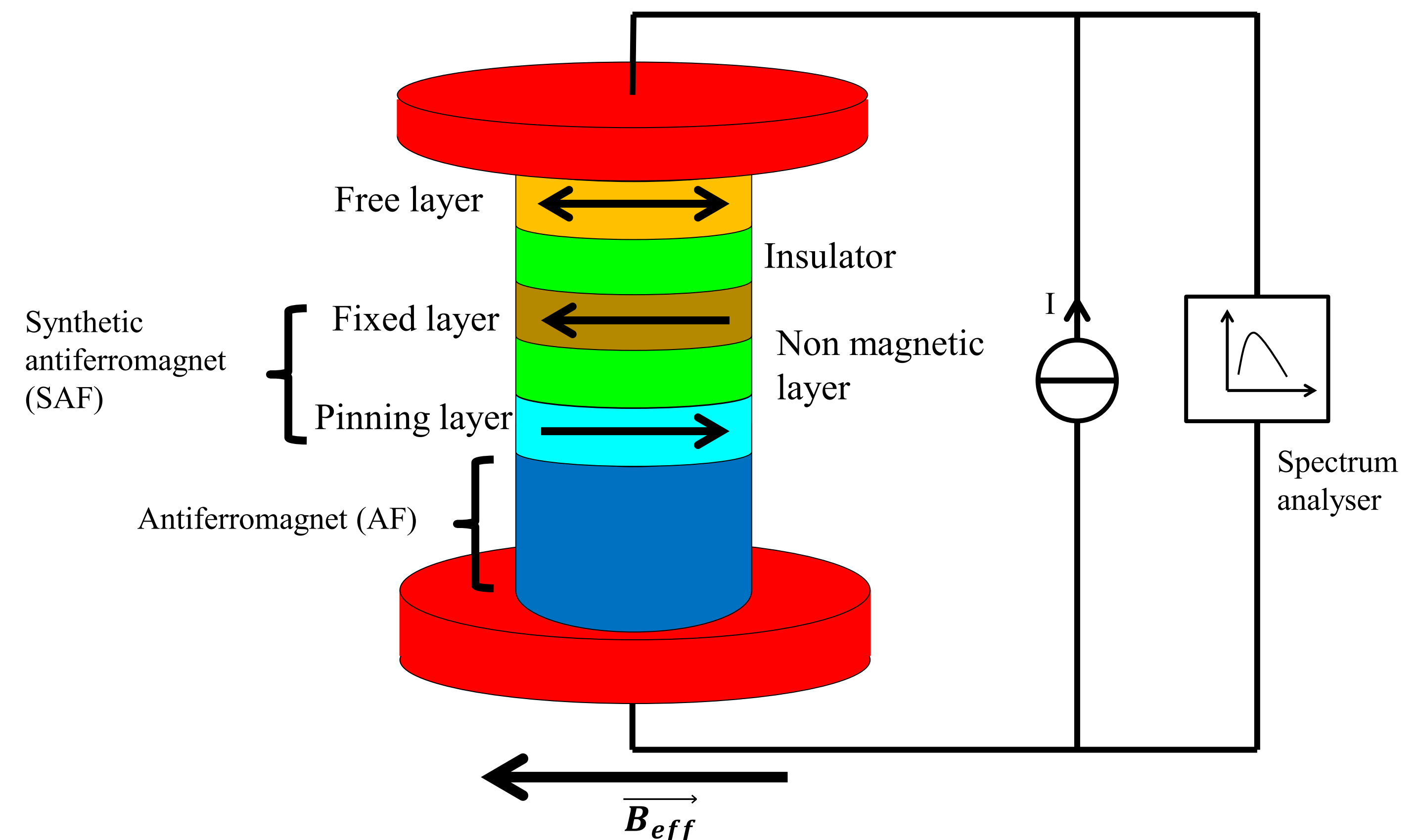
This work was performed at the Helmholtz Zentrum Dresden Rossendorf (HZDR) as part of an internship between the 1st of July 2013 and the 30th of August 2013

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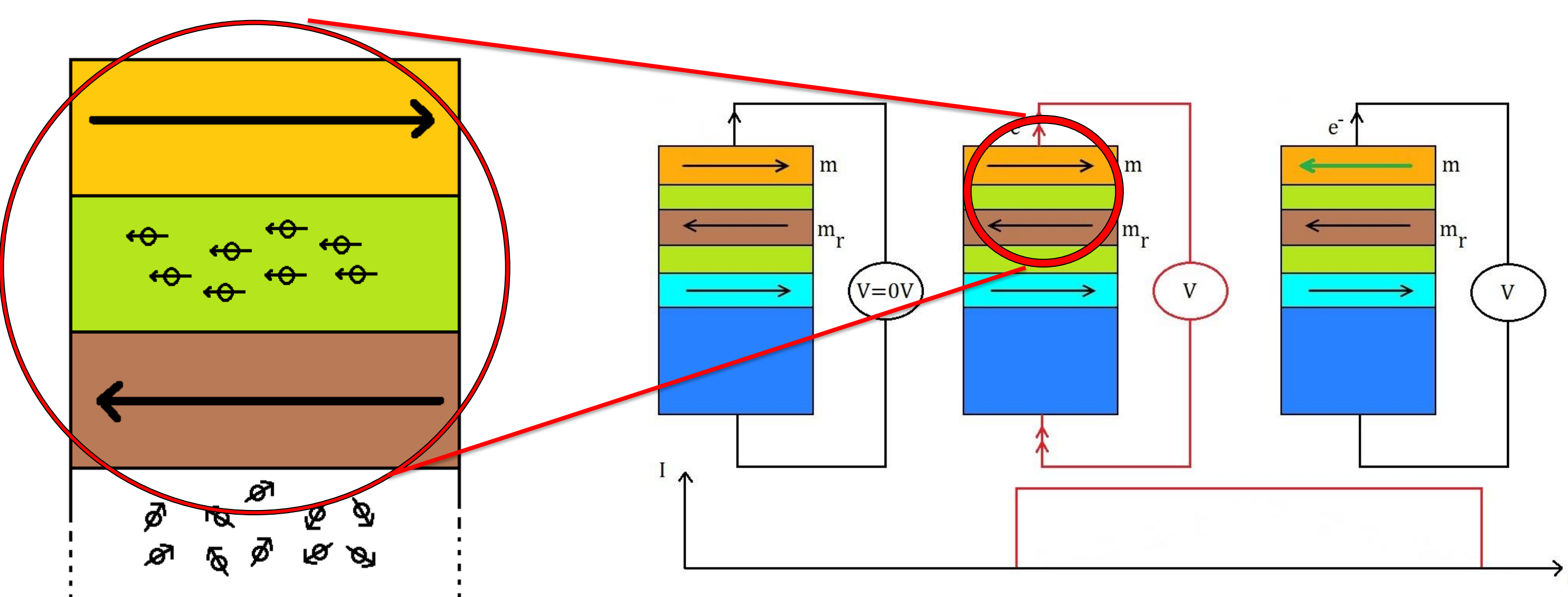
Motivation:

- A spin polarized current can exert a spin transfer torque to the magnetisation of a layer. [1]
- A better understanding of the magnetic behavior is required to achieve significant improvements in Magnetic Random Access Memory (MRAM) memories.
- Spin valve structure can act as a frequency tunable microwaves source or resonator whose output power is in the μW range [2]
- We present a way of measuring principal torque parameters in harmony with peer reviewed papers.

Spin-Valve structure and TE-FMR setup:



Spin Polarisation & Spin Transfer Torque (STT)



1. A current flowing through a polarized layer becomes spin polarized.

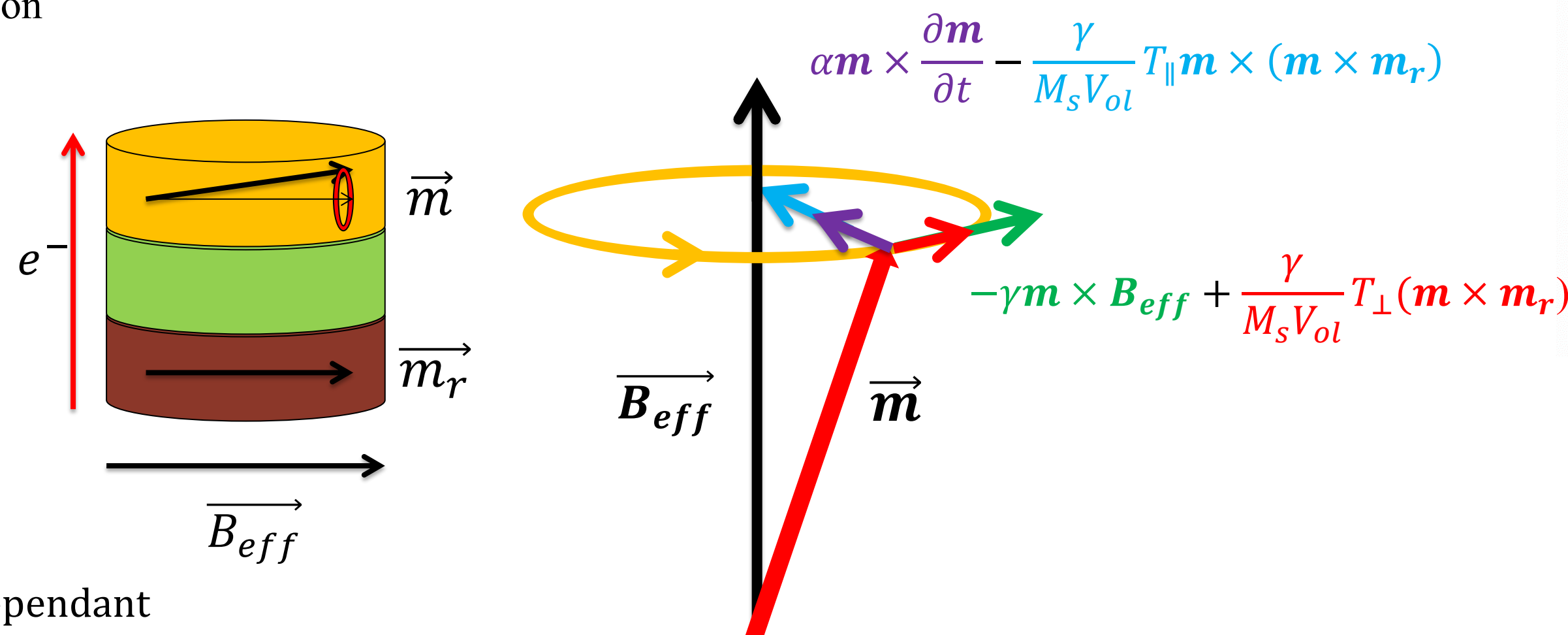
2. This current can transfer its polarization to the magnetisation of another layer and may switch it.

Landau-Lifshitz-Gilbert equation (LLG)

or how to describe the temporal magnetisation of a layer with both voltage and field applied ?

$$\frac{\partial \mathbf{m}}{\partial t} = \underbrace{-\gamma \mathbf{m} \times \mathbf{B}_{eff}}_{\text{Field torque}} + \underbrace{\alpha \mathbf{m} \times \frac{\partial \mathbf{m}}{\partial t}}_{\text{Damping}} - \underbrace{\frac{\gamma}{M_s V_{ol}} T_{\parallel} \mathbf{m} \times (\mathbf{m} \times \mathbf{m}_r)}_{\text{Spin Parallel Torque (damping like)}} + \underbrace{\frac{\gamma}{M_s V_{ol}} T_{\perp} (\mathbf{m} \times \mathbf{m}_r)}_{\text{Perpendicular torque (field like)}}$$

V_{ol} = Volume of the free layer
 M_s = saturation magnetisation
 α = damping factor



T_{\parallel} and T_{\perp} are voltage dependant

If we set : $a_{\parallel} V = \frac{T_{\parallel}}{M_s V_{ol}} = B_{\parallel}$

$a_{\perp} V^2 = \frac{T_{\perp}}{M_s V_{ol}} = B_{\perp}$

How to derive the parallel and the perpendicular torque parameters : a_{\parallel} and a_{\perp} ?

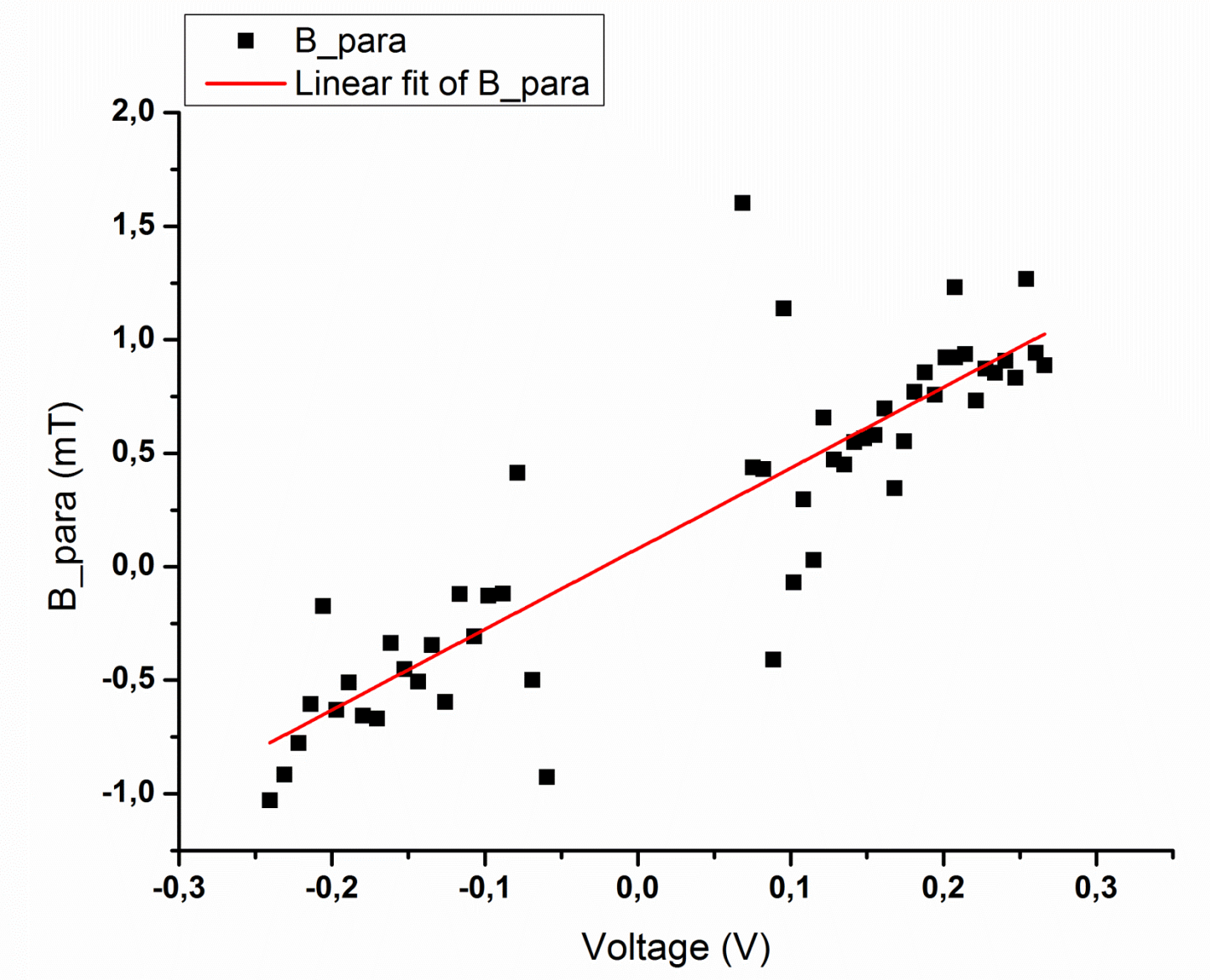
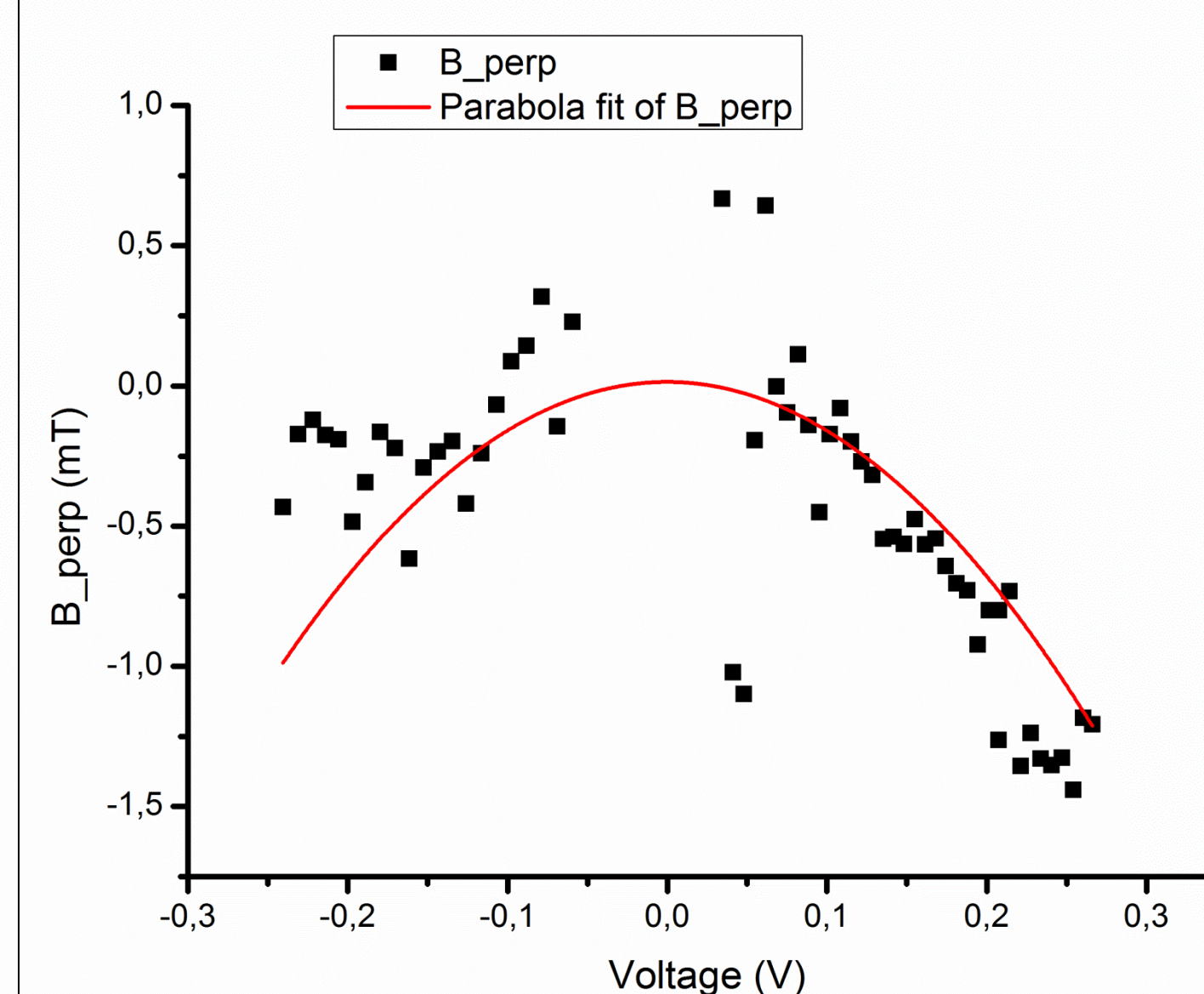
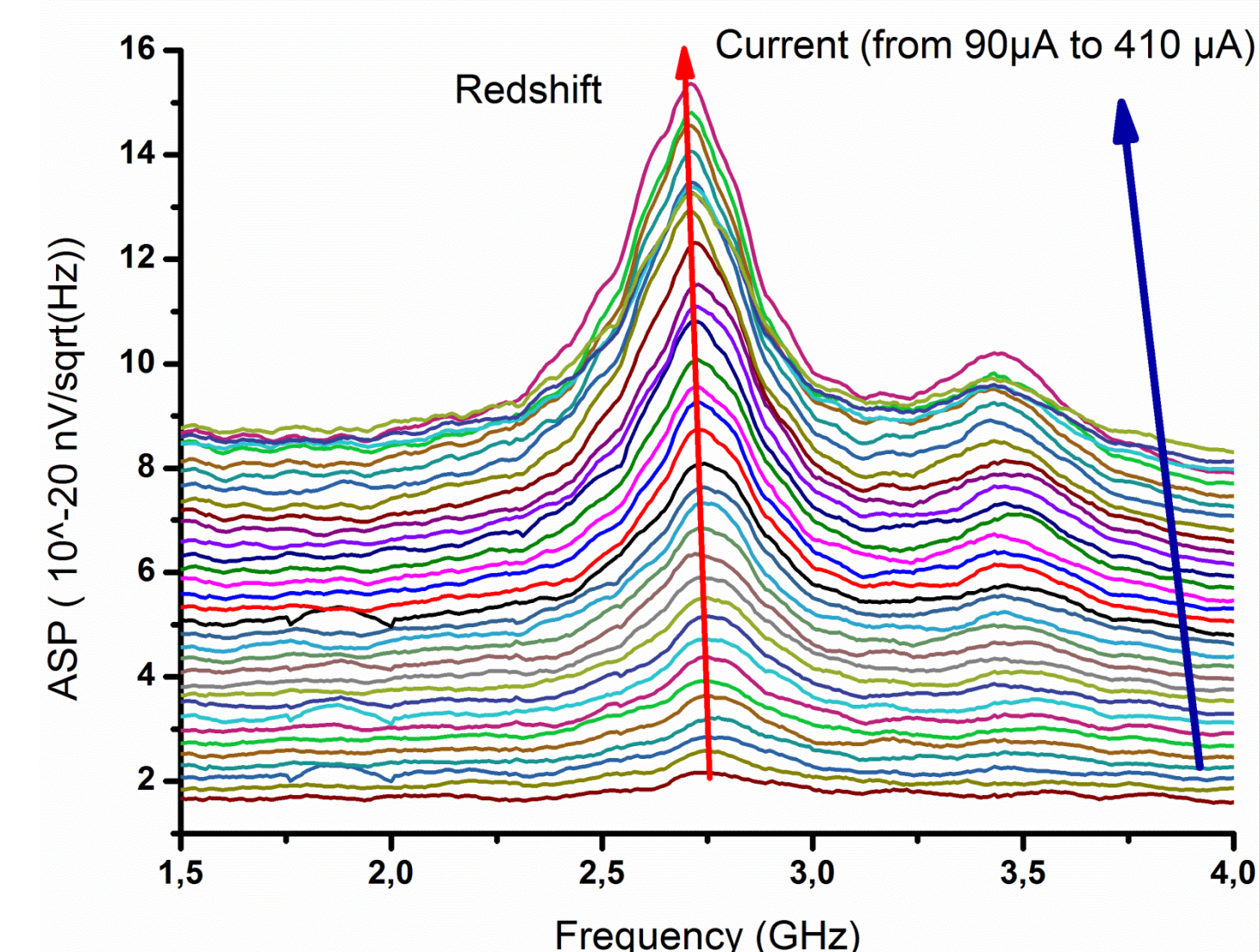
Method & Results

1. The resonance frequency and the width of the peak depend respectively on the perpendicular and parallel torque.

$$f = \frac{\gamma}{2\pi} \sqrt{(B_{eff} + \frac{T_{\perp}}{M_s V_{ol}})(B_{eff} + \frac{T_{\perp}}{M_s V_{ol}} + \mu_0 M_s)}$$

$$\Delta f = \frac{\gamma}{2\pi} (2B_{eff} + \mu_0 M_s) + \frac{\gamma}{2\pi} \frac{T_{\parallel}}{M_s V_{ol}}$$

2. From those formulas we can extract B_{\perp} (from the peak position) and B_{\parallel} (from the width of the peaks) as a function of the voltage.



From $a_{\perp} V^2 = \frac{T_{\perp}}{M_s V_{ol}} = B_{\perp}$

$T_{\perp} = 7,07 \times 10^{-20} \text{ J/V}^2$

From $a_{\parallel} V = \frac{T_{\parallel}}{M_s V_{ol}} = B_{\parallel}$

$T_{\parallel} = 1,45 \times 10^{-20} \text{ J/V}$

In harmony with paper [2] where $T_{\perp} = 20,9 \times 10^{-20} \text{ J/V}^2$ and $T_{\parallel} = 2,79 \times 10^{-19} \text{ J/V}$ was derived with the same method from similar structures.

Summary:

- The torque parameters were derived from a TE-FMR measurement and are in good agreement with the paper [1].
- Uncertainty for B_{eff} because it is composed of anisotropy, coupling, oersted, coercive and external fields.
- Difficult to measure accurate values for M_s which can lead to errors in the final measurement.

References:

- [1] M. D. Stiles, A. Zangwill *Anatomy of spin-transfer torque*. PHYSICAL REVIEW B 66, 014407 ~2002
- [2] Alina M. Deac et al. *Bias-Driven high-power microwave emission from MgO-based tunnel magnetoresistance devices*, nature physics, VOL 4, October 2008

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